

16-Mbit (2M x 8) MoBL[®] Static RAM

Features

- **Very high speed**
 - 55 ns
- **Wide voltage range**
 - 2.2V – 3.6V
- **Ultra-low active power**
 - Typical active current: 2 mA @ f = 1 MHz
 - Typical active current: 15 mA @ f = f_{Max} (55 ns Speed)
- **Ultra-low standby power**
- **Easy memory expansion with \overline{CE}_1 , \overline{CE}_2 and \overline{OE} features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Available in Pb-free and non Pb-free 48-ball VFBGA package**

Functional Description^[1]

The CY62168DV30 is a high-performance CMOS static RAMs organized as 2048Kbit words by 8 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL[®]) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly

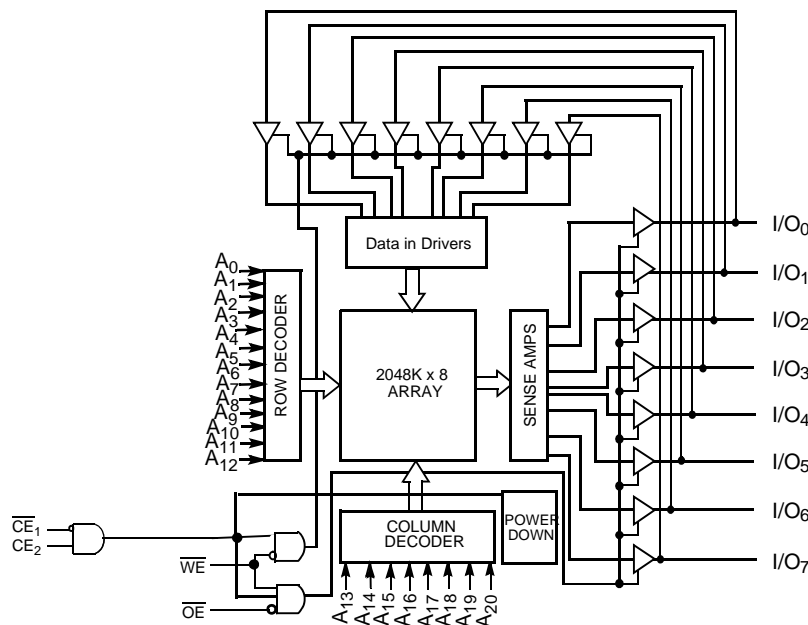
reduces power consumption. The device can be put into standby mode reducing power consumption by 90% when addresses are not toggling. The device can be put into standby mode reducing power consumption by more than 99% when deselected Chip Enable 1 (\overline{CE}_1) HIGH or Chip Enable 2 (\overline{CE}_2) LOW. The input/output pins (I/O₀ through I/O₇) are placed in a high-impedance state when: deselected Chip Enable 1 (\overline{CE}_1) HIGH or Chip Enable 2 (\overline{CE}_2) LOW, outputs are disabled (\overline{OE} HIGH), or during a write operation (Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (\overline{CE}_2) HIGH and WE LOW).

Writing to the device is accomplished by taking Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (\overline{CE}_2) HIGH and Write Enable (\overline{WE}) input LOW. Data on the eight I/O pins (I/O₀ through I/O₇) is then written into the location specified on the address pins (A₀ through A₂₀).

Reading from the device is accomplished by taking Chip Enable 1 (\overline{CE}_1) and Output Enable (\overline{OE}) LOW and Chip Enable 2 (\overline{CE}_2) HIGH while forcing Write Enable (\overline{WE}) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O₀ through I/O₇) are placed in a high-impedance state when the device is deselected (\overline{CE}_1 LOW and \overline{CE}_2 HIGH), the outputs are disabled (\overline{OE} HIGH), or during a write operation (\overline{CE}_1 LOW and \overline{CE}_2 HIGH and WE LOW). See the truth table for a complete description of read and write modes.

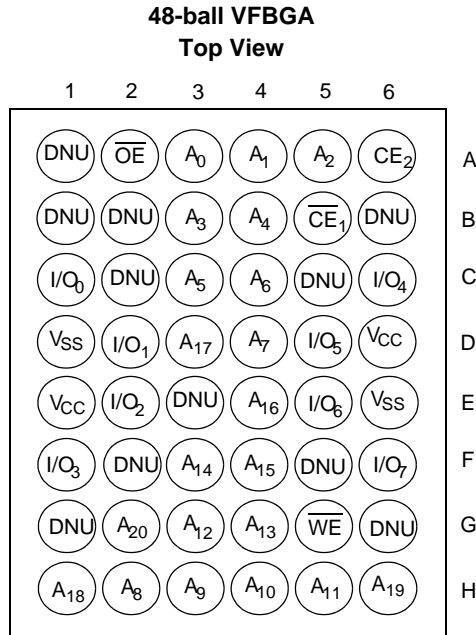
Logic Block Diagram



Note:

1. For best-practice recommendations, please refer to the Cypress application note entitled *System Design Guidelines*, available at <http://www.cypress.com>.

Pin Configuration^[2]



Product Portfolio

Product	V _{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I _{CC} (mA)				Standby I _{SB2} (μ A)	
	f = 1 MHz		f = f _{Max}							
	Min.	Typ. ^[3]	Max.		Typ. ^[3]	Max.	Typ. ^[3]	Max.	Typ. ^[3]	Max.
CY62168DV30LL	2.2	3.0	3.6	55	2	4	15	30	2.5	22

Notes:

- 2. DNU pins have to be left floating or tied to V_{SS} to ensure proper operation.
- 3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ.)}, T_A = 25°C.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C
 Ambient Temperature with Power Applied..... -55°C to +125°C
 Supply Voltage to Ground Potential -0.3V to $V_{CC(max)}$ + 0.3V
 DC Voltage Applied to Outputs in High-Z State^[4, 5] -0.3V to $V_{CC(max)}$ + 0.3V

DC Input Voltage^[4, 5] -0.3V to $V_{CC(max)}$ + 0.3V
 Output Current into Outputs (LOW)..... 20 mA
 Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)
 Latch-up Current..... > 200 mA

Operating Range

Range	Ambient Temperature (T_A) ^[6]	V_{CC} ^[7]
Industrial	-40°C to +85°C	2.2V – 3.6V

DC Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions	CY62168DV30-55			Unit	
			Min.	Typ. ^[3]	Max.		
V_{OH}	Output HIGH Voltage	$2.2V \leq V_{CC} \leq 2.7V$	$I_{OH} = -0.1 \text{ mA}$	2.0		V	
		$2.7V \leq V_{CC} \leq 3.6V$	$I_{OH} = -1.0 \text{ mA}$	2.4			
V_{OL}	Output LOW Voltage	$2.2V \leq V_{CC} \leq 2.7V$	$I_{OL} = 0.1 \text{ mA}$		0.4	V	
		$2.7V \leq V_{CC} \leq 3.6V$	$I_{OL} = 2.1 \text{ mA}$		0.4		
V_{IH}	Input HIGH Voltage	$2.2V \leq V_{CC} \leq 2.7V$		1.8	$V_{CC} + 0.3$	V	
		$2.7V \leq V_{CC} \leq 3.6V$		2.2	$V_{CC} + 0.3$		
V_{IL}	Input LOW Voltage	$2.2V \leq V_{CC} \leq 2.7V$		-0.3	0.6	V	
		$2.7V \leq V_{CC} \leq 3.6V$		-0.3	0.8		
I_{IX}	Input Leakage Current	$GND \leq V_I \leq V_{CC}$		-1	+1	μA	
I_{OZ}	Output Leakage Current	$GND \leq V_O \leq V_{CC}$, Output disabled		-1	+1	μA	
I_{CC}	V_{CC} Operating Supply Current	$f = f_{Max} = 1/t_{RC}$	$V_{CC} = 3.6V$, $I_{OUT} = 0 \text{ mA}$, CMOS level		15	30	mA
		$f = 1 \text{ MHz}$			2	4	
I_{SB1}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}_1 \geq V_{CC} - 0.2V$, $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$, $V_{IN} \leq 0.2V$, $f = f_{Max}$ (Address and Data Only), $f = 0$ (\overline{OE} , \overline{WE})			2.5	22	μA
I_{SB2}	Automatic CE Power-down Current— CMOS Inputs	$\overline{CE}_1 \geq V_{CC} - 0.2V$, $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, $f = 0$, $V_{CC} = 3.6V$			2.5	22	μA

Capacitance^[8]

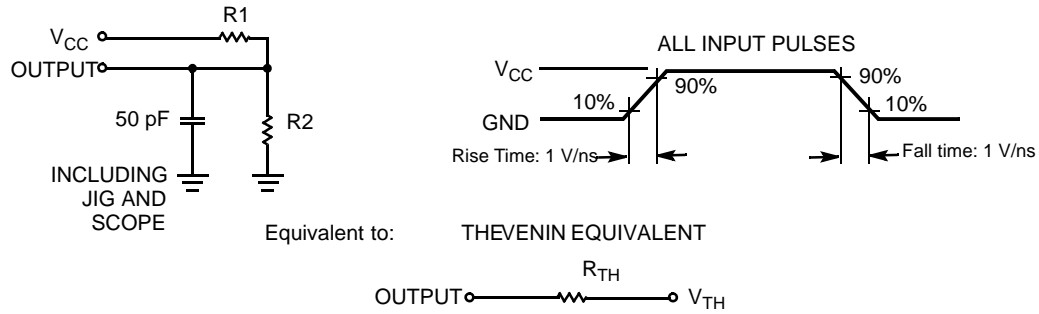
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$, $V_{CC} = V_{CC(typ.)}$	8	pF
C_{OUT}	Output Capacitance		10	pF

Notes:

4. $V_{IL(min)}$ = -2.0V for pulse durations less than 20 ns.
5. $V_{IH(max)}$ = $V_{CC} + 0.75V$ for pulse durations less than 20 ns.
6. T_A is the "Instant-On" case temperature.
7. Full device AC operation assumes a 100 μs ramp time from 0 to $V_{CC(min)}$ and 100 μs wait time after V_{CC} stabilization.
8. Tested initially and after any design or process changes that may affect these parameters.

Thermal Resistance^[8]

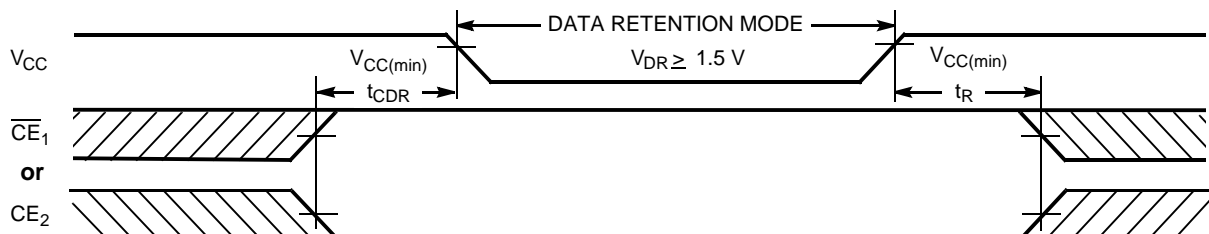
Parameter	Description	Test Conditions	VFBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 x 4.5 inch, 2-layer printed circuit board	55	$^{\circ}\text{C}/\text{W}$
Θ_{JC}	Thermal Resistance (Junction to Case)		16	$^{\circ}\text{C}/\text{W}$

AC Test Loads and Waveforms


Parameters	2.5V	3.0V	Unit
R1	16600	1103	Ω
R2	15400	1554	Ω
R _{TH}	8000	645	Ω
V _{TH}	1.2	1.75	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ. ^[3]	Max.	Unit
V _{DR}	V _{CC} for Data Retention		1.5		3.6	V
I _{CCDR}	Data Retention Current	V _{CC} = 1.5V $\overline{\text{CE}}_1 \geq V_{CC} - 0.2\text{V}$ or $\text{CE}_2 \leq 0.2\text{V}$ $V_{IN} \geq V_{CC} - 0.2\text{V}$ or $V_{IN} \leq 0.2\text{V}$			10	μA
t _{CDR} ^[8]	Chip Deselect to Data Retention Time		0			ns
t _R ^[9]	Operation Recovery Time		t _{RC}			ns

Data Retention Waveform

Note:

9. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min.)} ≥ 100 μs or stable at V_{CC(min.)} ≥ 100 μs .

Switching Characteristics Over the Operating Range ^[10]

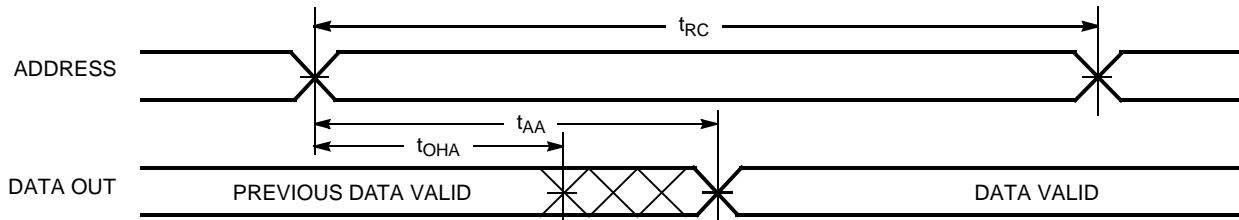
Parameter	Description	55 ns		Unit
		Min.	Max.	
Read Cycle				
t_{RC}	Read Cycle Time	55		ns
t_{AA}	Address to Data Valid		55	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	\overline{CE}_1 LOW and CE_2 HIGH to Data Valid		55	ns
t_{DOE}	\overline{OE} LOW to Data Valid		25	ns
t_{LZOE}	\overline{OE} LOW to Low Z ^[11]	5		ns
t_{HZOE}	\overline{OE} HIGH to High Z ^[11, 12]		20	ns
t_{LZCE}	\overline{CE}_1 LOW and CE_2 HIGH to Low Z ^[11]	10		ns
t_{HZCE}	\overline{CE}_1 HIGH or CE_2 LOW to High Z ^[11, 12]		20	ns
t_{PU}	\overline{CE}_1 LOW and CE_2 HIGH to Power-Up	0		ns
t_{PD}	\overline{CE}_1 HIGH or CE_2 LOW to Power-Down		55	ns
Write Cycle^[13]				
t_{WC}	Write Cycle Time	55		ns
t_{SCE}	\overline{CE}_1 LOW and CE_2 HIGH to Write End	40		ns
t_{AW}	Address Set-Up to Write End	40		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-Up to Write Start	0		ns
t_{PWE}	\overline{WE} Pulse Width	40		ns
t_{SD}	Data Set-Up to Write End	25		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	\overline{WE} LOW to High Z ^[11, 12]		20	ns
t_{LZWE}	\overline{WE} HIGH to Low Z ^[11]	10		ns

Notes:

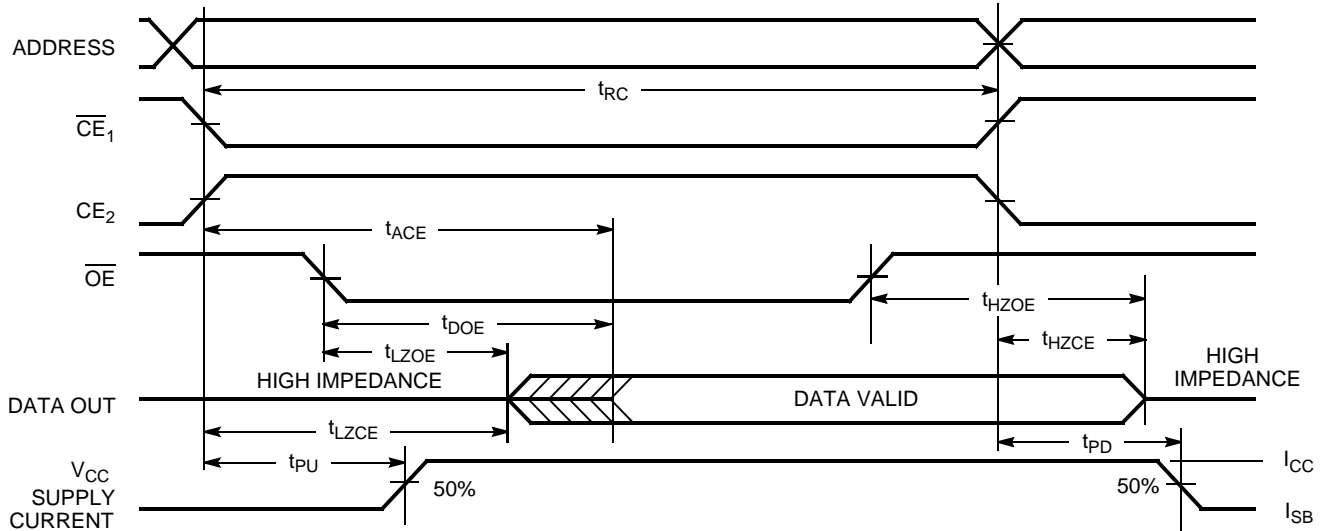
10. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3ns or less (1V/ns), timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" section.
11. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
12. t_{HZOE} , t_{HZCE} , and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
13. The internal write time of the memory is defined by the overlap of \overline{WE} , $\overline{CE}_1 = V_{IL}$, and $CE_2 = V_{IH}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

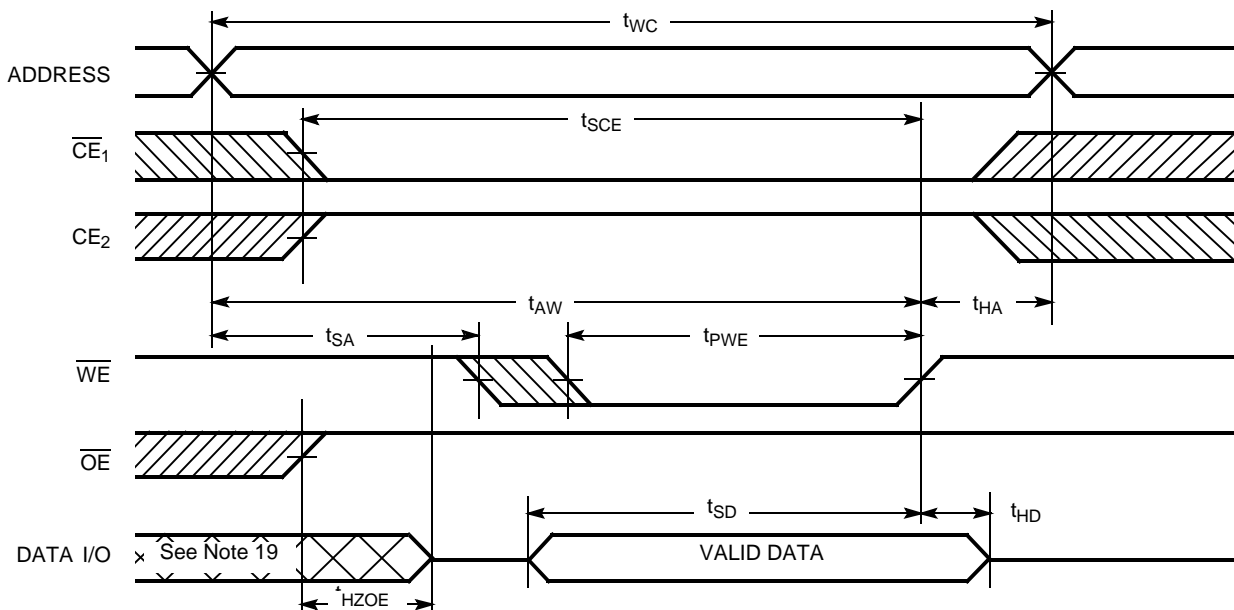
Read Cycle No. 1 (Address Transition Controlled)^[14, 15]



Read Cycle No. 2 (OE Controlled)^[15, 16]



Write Cycle No. 1 (WE Controlled)^[13, 17, 18]

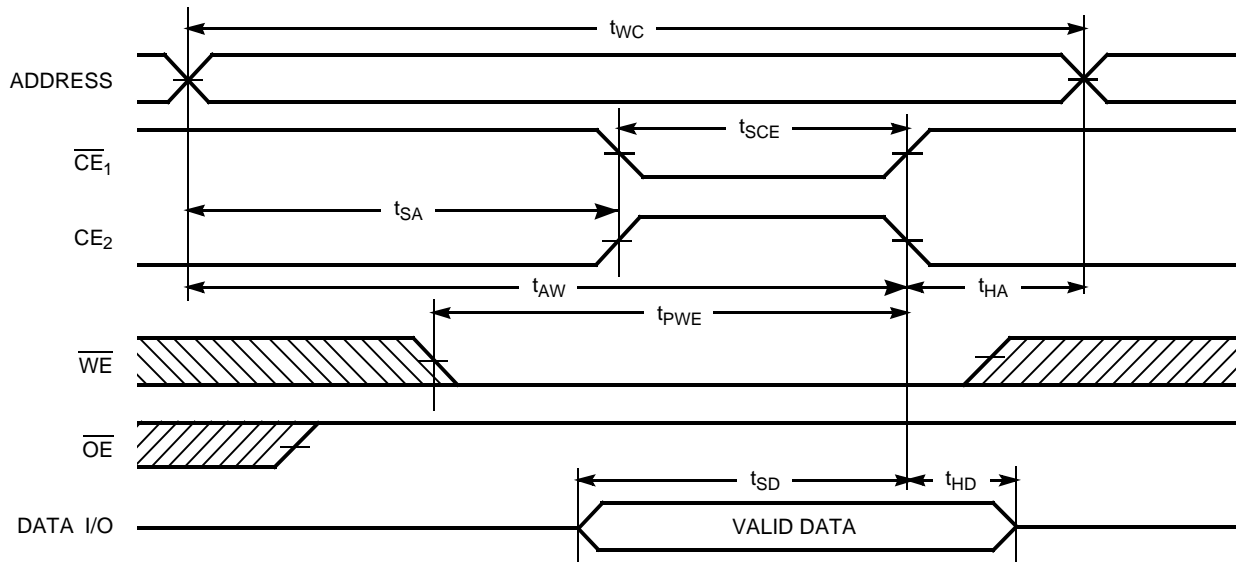


Notes:

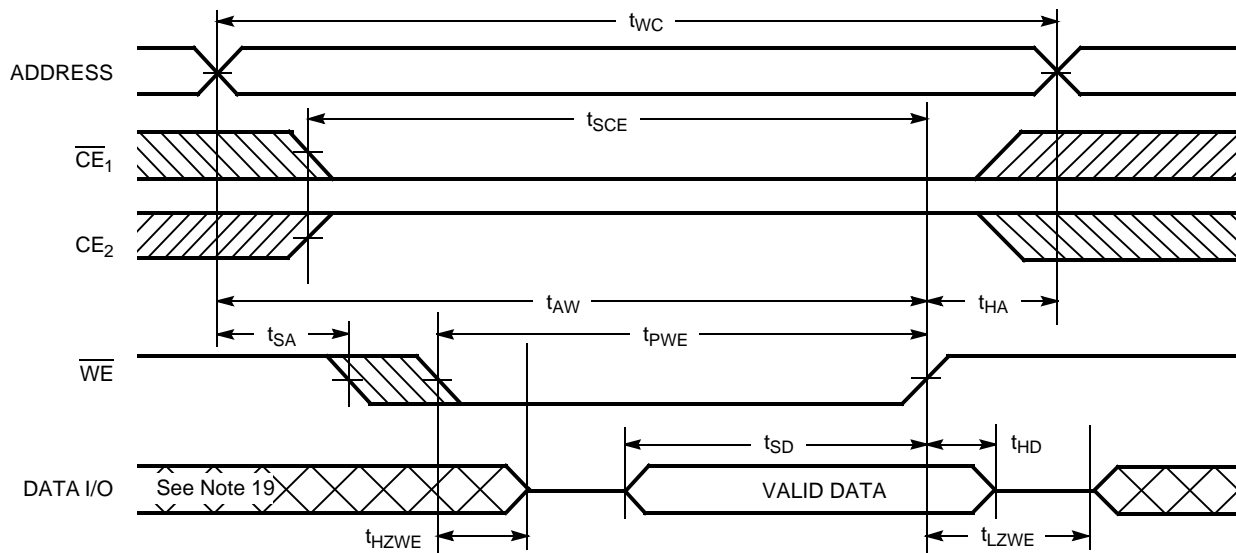
- 14. Device is continuously selected. \overline{OE} , $\overline{CE}_1 = V_{IL}$, $CE_2 = V_{IH}$.
- 15. \overline{WE} is HIGH for read cycle.
- 16. Address valid prior to or coincident with \overline{CE}_1 transition LOW and CE_2 transition HIGH.
- 17. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
- 18. If \overline{CE}_1 goes HIGH or CE_2 goes LOW simultaneously with \overline{WE} HIGH, the output remains in high-impedance state.
- 19. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle No. 2 (\overline{CE}_1 or CE_2 Controlled)^[13, 17, 18]



Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW)^[19]



Truth Table

\overline{CE}_1	CE_2	\overline{WE}	\overline{OE}	Inputs/Outputs	Mode	Power
H	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	L	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	Data Out (I/O ₀ -I/O ₇)	Read	Active (I_{CC})
L	H	L	X	Data in (I/O ₀ -I/O ₇)	Write	Active (I_{CC})
L	H	H	H	High Z	Output Disabled	Active (I_{CC})

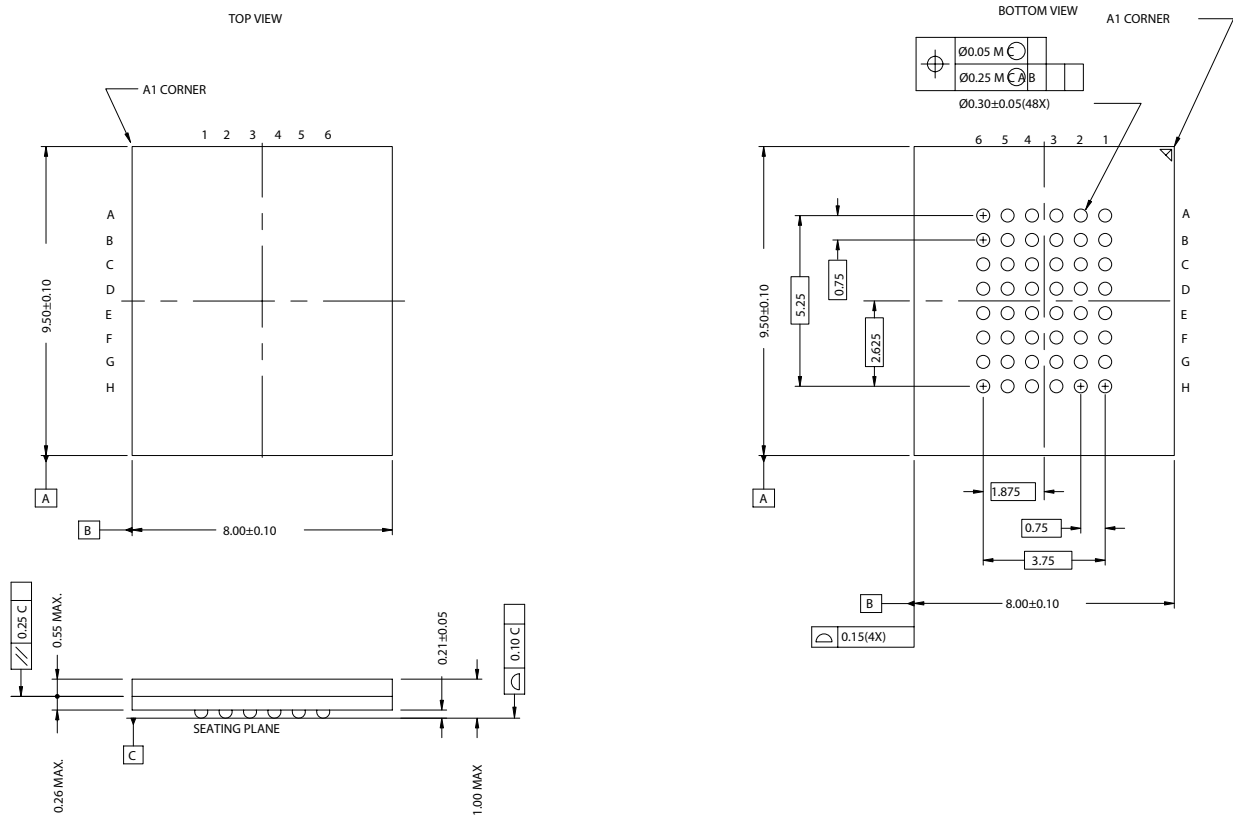
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
55	CY62168DV30LL-55BVI	51-85178	48-ball Fine Pitch BGA (8 x 9.5 x 1 mm)	Industrial
	CY62168DV30LL-55BVXI		48-ball Fine Pitch BGA (8 x 9.5 x 1 mm) (Pb-free)	

Please contact your local Cypress sales representative for availability of these parts

Package Diagram

48-ball VFBGA (8 x 9.5 x 1 mm) (51-85178)



51-85178-**

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Document History Page

Document Title: CY62168DV30 MoBL [®] , 16-Mbit (2M x 8) MoBL [®] Static RAM				
Document Number: 38-05329				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	118409	09/30/02	GUG	New Data Sheet
*A	123693	02/05/03	DPM	Changed Advance Information to Preliminary Added package diagram
*B	126556	04/24/03	DPM	Minor change: Change sunset owner from DPM to HRT
*C	132869	01/15/04	XRJ	Changed Preliminary to Final
*D	272589	See ECN	PCI	Updated Final data sheet and added Pb-free package.
*E	335864	See ECN	PCI	Removed redundant packages from Ordering Information Table Added Address A ₂₀ to ball G2 in the Pin Configuration
*F	492895	See ECN	VKN	Changed address of Cypress Semiconductor Corporation on Page# 1 from "3901 North First Street" to "198 Champion Court" Removed 70 ns speed bin Removed L power bin from product offering Updated Ordering Information Table